

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 20, line 14, as follows:

In Fig. 4, a distance A from bottom ends of the discharge ports for the dopant element ~~gaseous titanium~~ compound and the atmospheric gas to the surface of the silicon substrate 1 was set to 4 mm, for example, and a distance B from a bottom end of the discharge port for the gaseous titanium ~~dopant element~~ compound and the atmospheric gas to the surface of the silicon substrate 1 was set to 14 mm, for example. The difference between A and B was 10 mm.